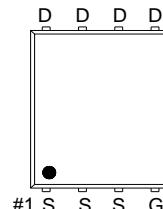
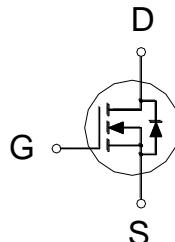


NIKO-SEM
**N-Channel Enhancement Mode
Field Effect Transistor**
**PK6B2BA
PDFN 5x6P
Halogen-Free & Lead-Free**
PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
30V	6mΩ	52A

**ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ Unless Otherwise Noted)**

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ³	$T_C = 25^\circ\text{C}$	I_D	52	A
	$T_C = 100^\circ\text{C}$		33	
Pulsed Drain Current ¹		I_{DM}	120	
Continuous Drain Current	$T_A = 25^\circ\text{C}$	I_D	18	
	$T_A = 70^\circ\text{C}$		14	
Avalanche Current		I_{AS}	25	
Avalanche Energy	$L = 0.1\text{mH}$	E_{AS}	31	mJ
Power Dissipation	$T_C = 25^\circ\text{C}$	P_D	31	
	$T_C = 100^\circ\text{C}$		12	
Power Dissipation ⁴	$T_A = 25^\circ\text{C}$	P_D	3.9	W
	$T_A = 70^\circ\text{C}$		2.5	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE		SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$t \leq 10\text{s}$	$R_{\theta JA}$	32	57	°C / W
Junction-to-Ambient ²	Steady-State	$R_{\theta JA}$			
Junction-to-Case	Steady-State	$R_{\theta JC}$			

¹Pulse width limited by maximum junction temperature.²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.³Package limitation current is 35A.⁴The Power dissipation is based on $R_{\theta JA} t \leq 10\text{s}$ value

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	30			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.3	1.6	2.3	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 24V, V _{GS} = 0V			1	μA
		V _{DS} = 20V, V _{GS} = 0V, T _J = 55 °C			10	
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 4.5V, I _D = 13A		5.2	8.5	mΩ
		V _{GS} = 10V, I _D = 13A		3.9	6	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 13A		86		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 15V, f = 1MHz		979		pF
Output Capacitance	C _{oss}			192		
Reverse Transfer Capacitance	C _{rss}			117		
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		1.85		Ω
Total Gate Charge ²	Q _g	V _{GS} = 10V		21		nC
		V _{GS} = 4.5V	V _{DS} = 15V, V _{GS} = 10V, I _D = 13A	11		
Gate-Source Charge ²	Q _{gs}			2.3		
Gate-Drain Charge ²	Q _{gd}			6		
Turn-On Delay Time ²	t _{d(on)}	V _{DS} = 15V, I _D ≈ 13A, V _{GS} = 10V, R _{GEN} = 6Ω		17.2		nS
Rise Time ²	t _r			10		
Turn-Off Delay Time ²	t _{d(off)}			36.8		
Fall Time ²	t _f			10		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)						
Continuous Current	I _S				25	A
Forward Voltage ¹	V _{SD}	I _F = 13A, V _{GS} = 0V			1.2	V
Reverse Recovery Time	t _{rr}	I _F = 13A, dI _F /dt = 100A / μS		11.5		nS
Reverse Recovery Charge	Q _{rr}			2		nC

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

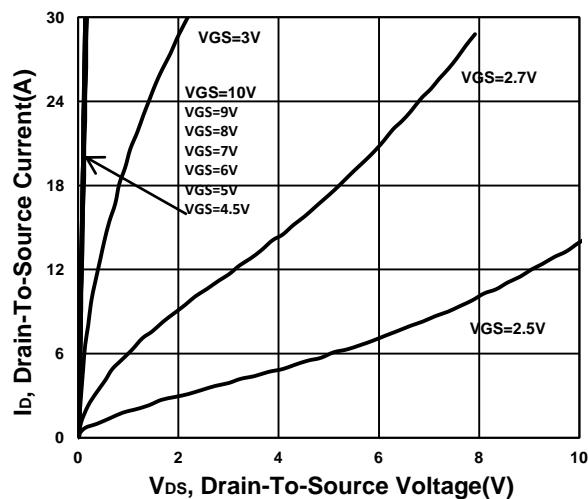
²Independent of operating temperature.

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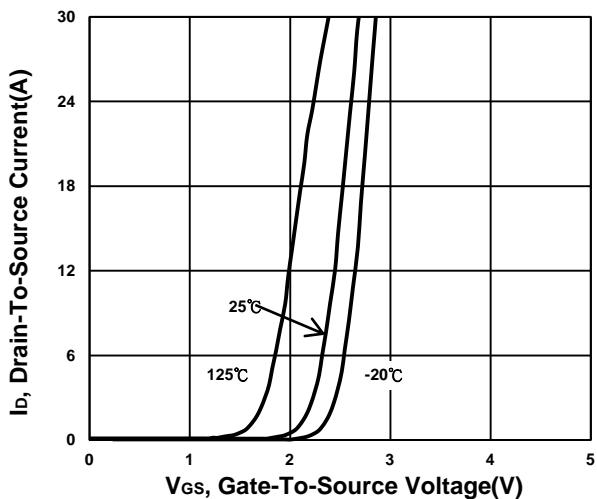
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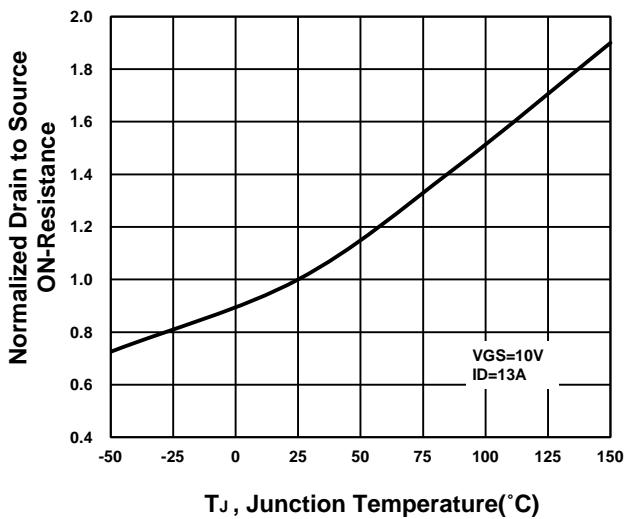
Output Characteristics



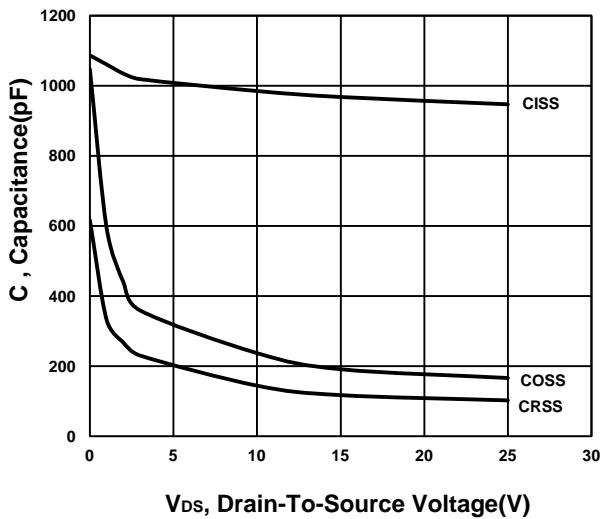
Transfer Characteristics



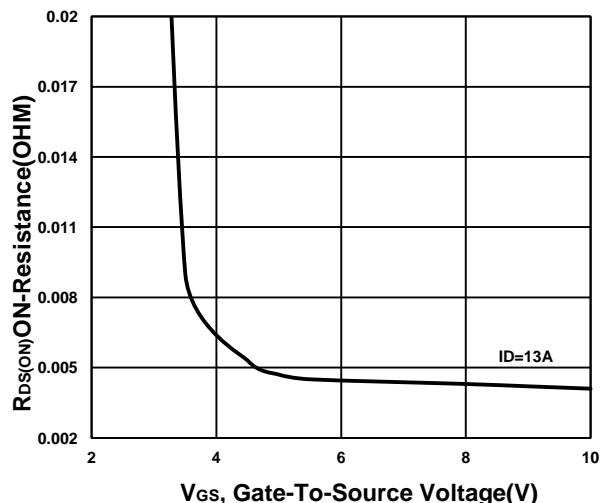
On-Resistance VS Temperature



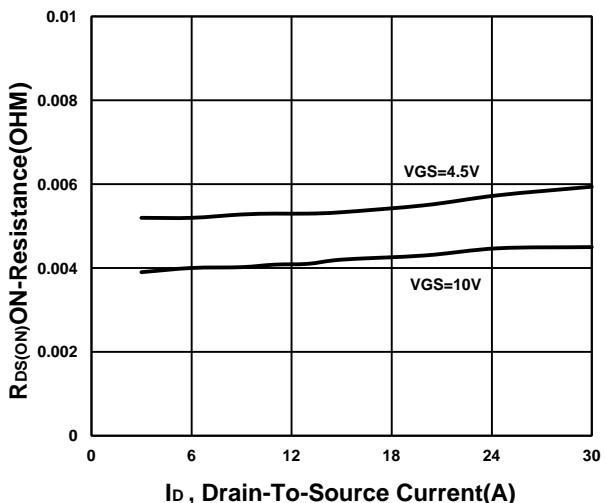
Capacitance Characteristic

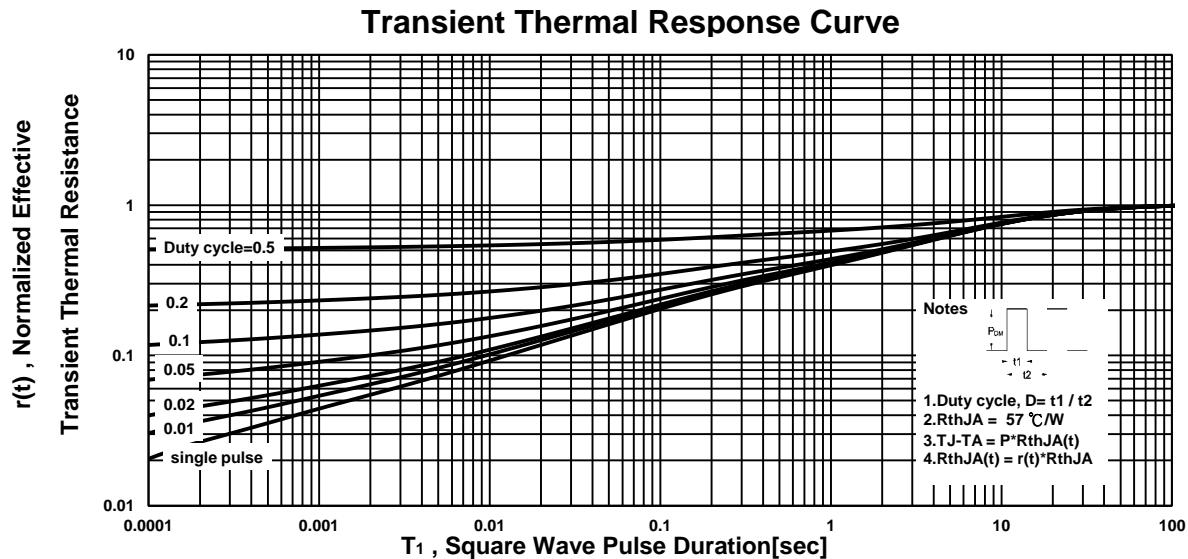
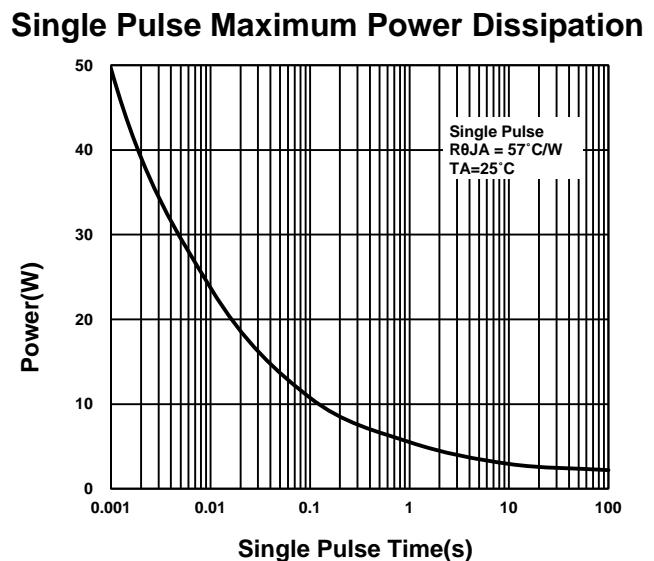
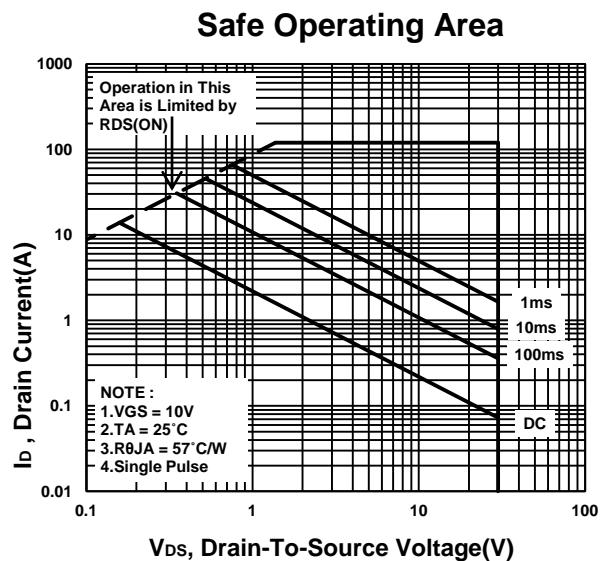
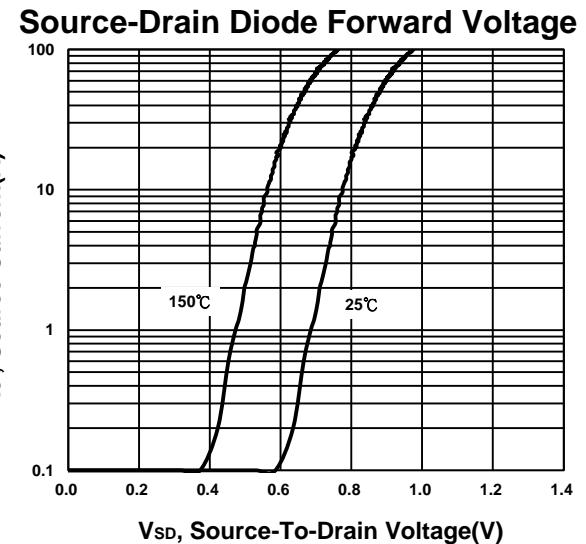
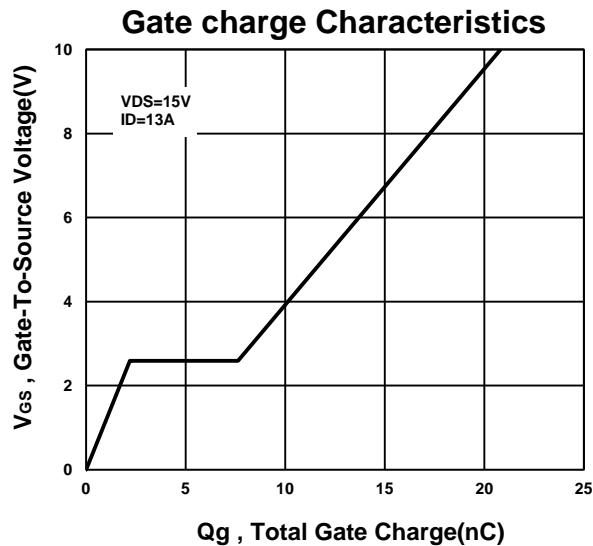


On-Resistance VS Gate-To-Source



On-Resistance VS Drain Current



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